

#### **Features and Benefits**

- Integrated on-time control circuit (it realizes high power factor by average current control)
- Integrated startup circuit (no external startup circuit necessary)
- Integrated soft-start circuit (reduces power stress during start-up on the incorporated power MOSFET and output rectifier)
- Integrated bias assist circuit (improves startup performance, suppresses VCC voltage droop during operation, and allows use of low-rated ceramic capacitor on VCC pin)
- Integrated Leading Edge Blanking (LEB) circuit
- Integrated maximum on-time limit circuit
- Protection features:
- Overcurrent protection (OCP): pulse-by-pulse
- Overvoltage protection (OVP): latched shutdown
- Overload protection (OLP): latched shutdown
- <sup>n</sup> Thermal shutdown (TSD): latched shutdown

### Description

The LC5540LF series is the power IC for the isolated type LED driver which has an incorporated power MOSFET, designed for input capacitorless applications, and making it possible for systems to comply with the harmonics standard (IEC61000-3-2 class C), even during light load condition. The controller adapts the average current control method for realizing high power factors, and the quasi-resonant topology contributes to high efficiency and low EMI noise. The series is housed in TO-220 packages. The rich set of protection features helps to realize low component counts, and high performance-to-cost power supply.

The incorporated MOSFET has a  $V_{DSS}(min)$  rating from 650 V (LC5546LF and LC5547LF) to 800 V (LC5549LF). The  $R_{DS(on)}(max)$  is  $1.1~\Omega$  (LC5547LF) to  $1.9~\Omega$  (LC5546LF). It is capable of a maximum output power of 80 W on 230 VAC supply to 55 W on universal input supply (85 to 265VAC) (LC5547LF) based on the thermal rating. Note that the maximum output power can be up to 120% to 140% of this value. However, it may be limited in applications with low output voltage or short duty cycle.

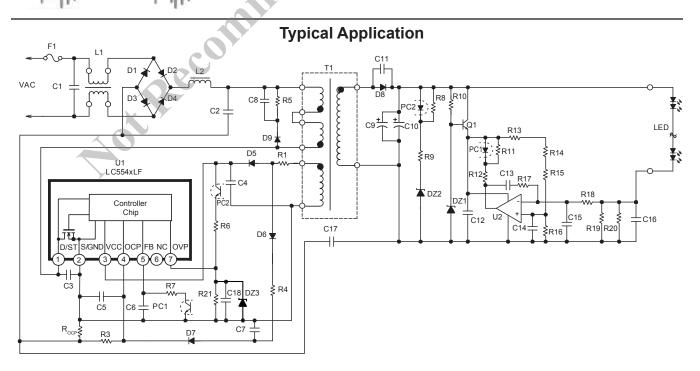
### Packages: 7-pin TO-220F





### **Applications**

- LED lighting fixtures
- LED light bulbs



#### **Selection Guide**

Part	art MOSFET		PWM Operation	On-Time	P <sub>0</sub>		
Number	V <sub>DSS</sub> (min) (V)	(max) (Ω)	Frequency, f <sub>OSC</sub> (typ) (kHz)	t <sub>ON(MAX)</sub> (typ) (µs)	230 VAC	85 to 265 VAC	
LC5546LF	650	1.9		60 40	40	]	
LC5547LF	050	1.1	40	17.5	80	55	
LC5549LF	800	1.7			60	40	
	owever, maxi	mum outp	lowable maximum output out power may be limited i	•	•		
The polarity v	alue for curre	ent specifi	es a sink as "+," and a so	ource as "-," refe	erencing the	IC.	
Absolute I	Maximum	Ratings	s Unless specifically no	oted, T <sub>A</sub> is 25°	С	40	

<sup>\*</sup>Based on the thermal rating; the allowable maximum output power can be up to 120% to 140% of this value. However, maximum output power may be limited in such an application with low output voltage or short duty cycle.

### Absolute Maximum Ratings Unless specifically noted, TA is 25°C

Characteristic	Symbol		Notes	Pins	Rating	Unit
		LC5546LF	, , , , , , , , , , , , , , , , , , ,		9.2	А
Drain Current <sup>1</sup>	I <sub>DPeak</sub>	LC5547LF	Single pulse	1 – 2	13.0	Α
		LC5549LF			10.5	Α
		LC5546LF	I <sub>LPeak</sub> = 2.9A, V <sub>DD</sub> = 99 V, L = 20 mH		99	mJ
Single Pulse Avalanche Energy <sup>2</sup>	E <sub>AS</sub>	LC5547LF	I <sub>LPeak</sub> = 4.4A, V <sub>DD</sub> = 99 V, L = 20 mH	1 – 2	233	mJ
		LC5549LF	I <sub>LPeak</sub> = 2.8A, V <sub>DD</sub> = 99 V, L = 20 mH		92	mJ
Control Part Input Voltage	V <sub>CC</sub>		<b>O</b> *	3 – 2	35	V
OCP Pin Voltage	V <sub>OCP</sub>			4 – 2	-2.0 to 5.0	V
FB Pin Voltage	$V_{FB}$			5 – 2	-0.3 to 7.0	V
OVP Pin Voltage	V <sub>OVP</sub>			7 – 2	-0.3 to 5.0	V
		LC5546LF			20.2	W
Allowable Power Dissipation of	P <sub>D1</sub>	LC5547LF	With infinite heatsink	1 – 2	23.6	W
MOSFET <sup>3</sup>	PD1	LC5549LF				
		Without heatsink			1.8	W
Internal Frame Temperature in Operation	T <sub>F</sub>			_	-20 to 115	°C
Operating Ambient Temperature	T <sub>OP</sub>			_	-55 to 115	°C
Storage Temperature	T <sub>stg</sub>			_	-55 to 125	°C
Channel Temperature	T <sub>ch</sub>			_	150	°C

<sup>&</sup>lt;sup>1</sup>Refer to MOSFET Safe Operating Area Curve.

<sup>&</sup>lt;sup>2</sup>Refer to MOSFET Avalanche Energy Derating Coefficient Curve.

<sup>&</sup>lt;sup>3</sup>Refer to MOSFET Temperature versus Power Dissipation Curve.

### **Electrical Characteristics of Control Part** Unless specifically noted, $T_A$ is 25°C, $V_{CC}$ = 20 V

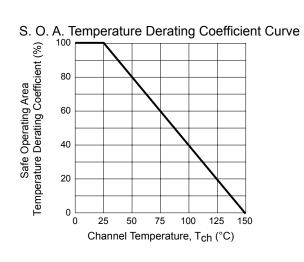
Characteristic	Symbol	Test Conditions	Pins	Min.	Тур.	Max.	Unit
Power Supply Startup Operation	•		'				
Operation Start Voltage	V <sub>CC(ON)</sub>		3 – 2	13.8	15.1	17.3	V
Operation Stop Voltage*	V <sub>CC(OFF)</sub>		3 – 2	8.4	9.4	10.7	V
Circuit Current in Operation	I <sub>CC(ON)</sub>		3 – 2	_	-21	4.7	mA
Startup Circuit Operation Voltage	V <sub>STARTUP</sub>		1 – 2	18	21	24	V
Startup Current	I <sub>CC(STARTUP)</sub>	V <sub>CC</sub> = 13 V	3 – 2	-8.5	-4.0	-1.5	mA
Startup Current Threshold Biasing Voltage*	V <sub>CC(BIAS)</sub>		3 – 2	9.5	11.0	12.5	V
Normal Operation				4			
PWM Operation Frequency	f <sub>OSC</sub>		1 – 2	33	40	47	kHz
Maximum On-Time	t <sub>ON(MAX)</sub>		1-2	14	17.5	21	μs
FB Pin Control Minimum Voltage	V <sub>FB(MIN)</sub>	A	5-2	0.50	0.85	1.20	V
Maximum Feedback Current	I <sub>FB(MAX)</sub>		5-2	-40	-25	-10	μΑ
Leading Edge Blanking Time	t <sub>ON(LEB)</sub>		4 – 2	-	600	-	ns
Quasi-Resonant Operation Threshold Voltage-1	V <sub>BD(TH1)</sub>		4 – 2	0.14	0.24	0.34	V
Quasi-Resonant Operation Threshold Voltage-2	V <sub>BD(TH2)</sub>	460	4 – 2	0.11	0.16	0.21	V
Protection Operation							
OCP Pin Overcurrent Protection (OCP) Threshold Voltage	V <sub>OCP</sub>		4 – 2	-0.66	-0.60	-0.54	V
OCP Pin Source Current	I <sub>OCP</sub>		4 – 2	-120	-40	-10	μΑ
OCP Pin Overvoltage Protection (OVP) Operation Voltage	V <sub>BD(OVP)</sub>		4 – 2	2.2	2.6	3.0	V
Overload Protection (OLP) Threshold Voltage	V <sub>FB(OLP)</sub>		5 – 2	4.1	4.5	4.9	V
OVP Pin OVP Threshold Voltage	V <sub>OVP(OVP)</sub>		7 – 2	1.6	2.0	2.4	V
VCC Pin OVP Threshold Voltage	V <sub>CC(OVP)</sub>		3 – 2	28.5	31.5	34.0	V
Thermal Shutdown Activating Temperature	T <sub>J(TSD)</sub>		_	135	-	-	°C

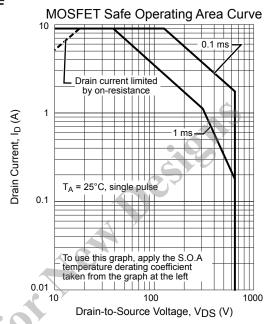
 $V_{CC(BIAS)} > V_{CC(OFF)}$  always.

### Electrical Characteristics of MOSFET Unless specifically noted, TA is 25°C

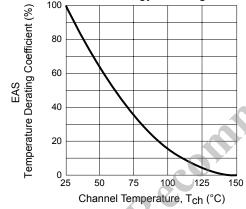
	Symbol	Tes	t Conditions	Pins	Min.	Тур.	Max.	Unit
Orain-to-Source Breakdown Voltage	V <sub>DSS</sub>	LC5546LF LC5547LF		1 – 2	650	_	_	V
		LC5549LF			800	_	<u> </u>	V
Orain Leakage Current	I <sub>DSS</sub>			1 – 2	_	<	300	μΑ
		LC5546LF		1 – 2	_	. 6.	1.9	Ω
On-Resistance	$R_{DS(ON)}$	LC5547LF			_		1.1	Ω
		LC5549LF			- 0	<b>R</b> -	1.7	Ω
Switching Time	t <sub>f</sub>	LC5546LF LC5547LF		1 – 2		_	400	ns
-		LC5549LF			<u> </u>	_	300	ns
		LC5546LF		40		_	3.1	°C/W
Thermal Resistance*	$R_{\theta ch-F}$	LC5547LF LC5549LF	A	Fo	_	_	2.2	°C/W
The thermal resistance between the ch		Mei						

# Characteristic Performance LC5546LF

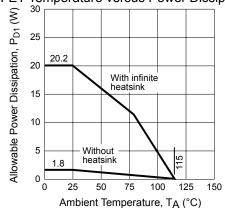


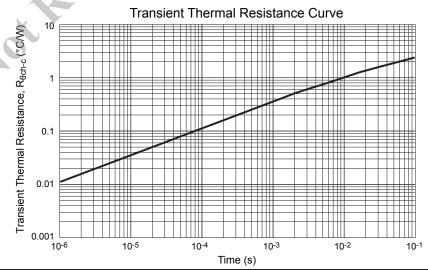


### MOSFET Avalanche Energy Derating Coefficient Curve



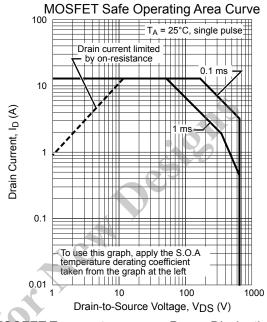
### MOSFET Temperature versus Power Dissipation Curve





# Characteristic Performance LC5547LF

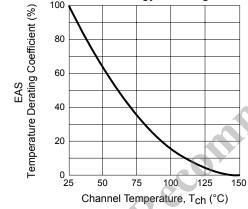
S. O. A. Temperature Derating Coefficient Curve



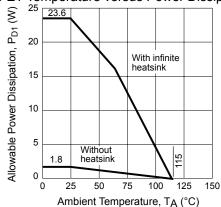
### MOSFET Avalanche Energy Derating Coefficient Curve

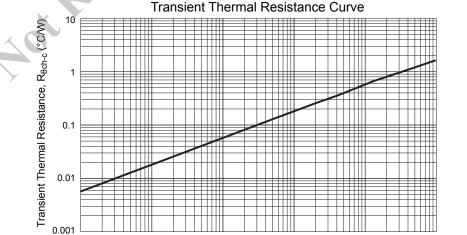
10-6

10-5



### MOSFET Temperature versus Power Dissipation Curve





10-4

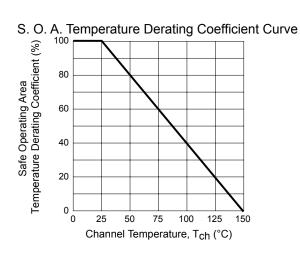
Time (s)

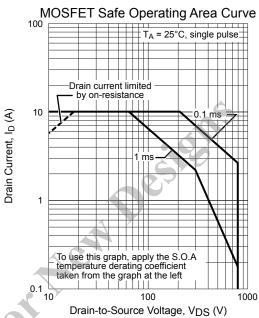
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10-2

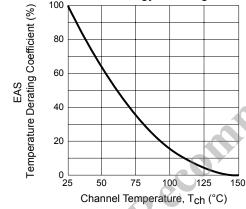
10-1

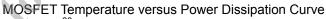
# Characteristic Performance LC5549LF

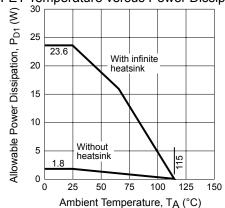


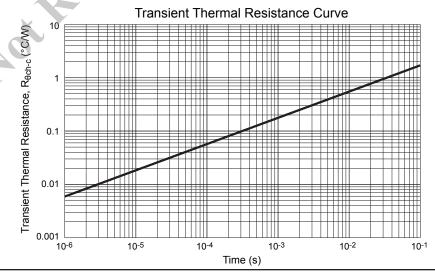


MOSFET Avalanche Energy Derating Coefficient Curve

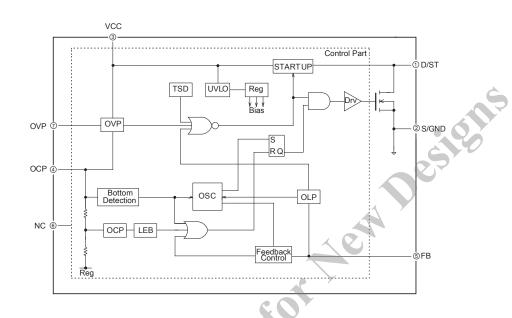








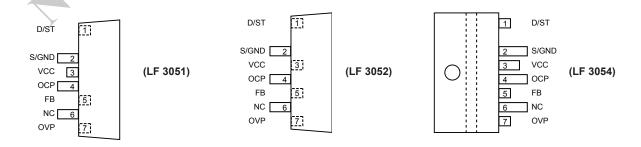
### **Functional Block Diagram**



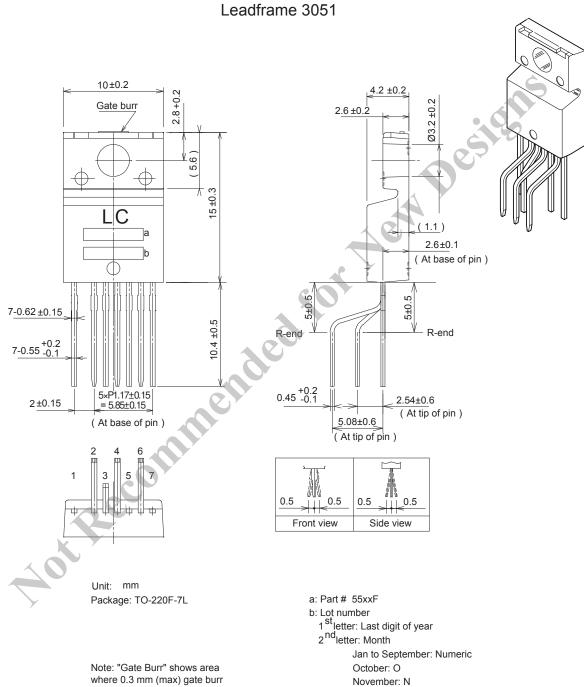
#### **Pin List Table**

Number	Name	Function
1	D/ST	MOSFET drain pin and input of the startup current
2	S/GND	MOSFET source and GND pin for the Control Part
3	VCC	Supply voltage input and Overvoltage protection (OVP) signal input
4	OCP	Overcurrent Protection, quasi-resonant signal input pin, and Overvoltage Protection (OVP) signal input
5	FB	Feedback signal input and Overload Protection (OLP) signal input
6	NC	No connection
7	OVP	Overvoltage Protection (OVP) signal input

### **Pin-out Diagrams**



## Package Outline Drawing



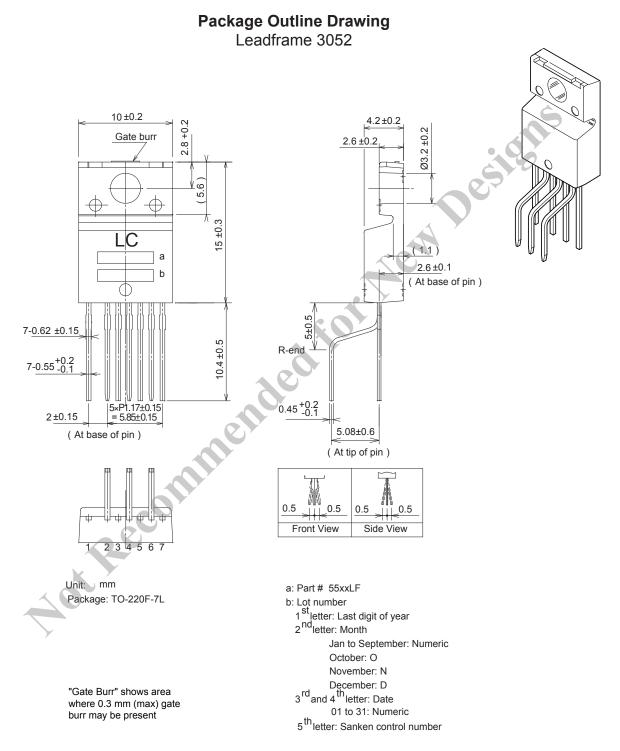
Pin treatment Pb-free. Device composition compliant with the RoHS directive.

may be present.

December: D 3 rd and 4 th letter: Date

01 to 31: Numeric

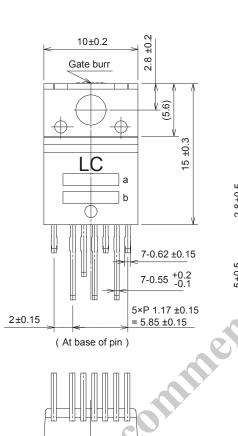
5<sup>th</sup>letter: Sanken control number

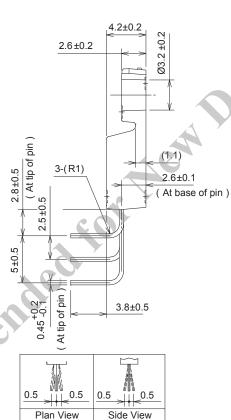


Pin treatment Pb-free. Device composition compliant with the RoHS directive.

## Package Outline Drawing

Leadframe 3054





1 2 3 4 5 6 7

Unit: mm Package: TO-220F-7L

"Gate Burr" shows area where 0.3 mm (max) gate burr may be present a: Part # 55xxLF
b: Lot number

1<sup>St</sup> letter: Last digit of year
2<sup>nd</sup> letter: Month

Jan to September: Numeric
October: O
November: N
December: D

3<sup>rd</sup> and 4<sup>th</sup> letter: Date
01 to 31: Numeric
5<sup>th</sup> letter: Sanken control number

Pin treatment Pb-free. Device composition compliant with the RoHS directive.

## LC5540LF Series

## Single-Stage Power Factor Corrected Off-Line Switching Regulator ICs

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

#### **Cautions for Storage**

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40% to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of the products that have been stored for a long time.

#### **Cautions for Testing and Handling**

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between the product pins, and wrong connections. Ensure all test parameters are within the ratings specified by Sanken for the products.

#### Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting the products on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce excess stress.
- Volatile-type silicone greases may crack after long periods of time, resulting in reduced heat radiation effect. Silicone greases with low consistency (hard grease) may cause cracks in the mold resin when screwing the products to a heatsink.

Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Туре	Suppliers
G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials Inc.
SC102	Dow Corning Toray Co., Ltd.

#### Cautions for Mounting to a Heatsink

When the flatness around the screw hole is insufficient, such as when
mounting the products to a heatsink that has an extruded (burred)
screw hole, the products can be damaged, even with a lower than

- recommended screw torque. For mounting the products, the mounting surface flatness should be 0.05 mm or less.
- Please select suitable screws for the product shape. Do not use
  a flat-head machine screw because of the stress to the products.
  Self-tapping screws are not recommended. When using self-tapping
  screws, the screw may enter the hole diagonally, not vertically,
  depending on the conditions of hole before threading or the work
  situation. That may stress the products and may cause failures.
- For tightening screws, if a tightening tool (such as a driver) hits the
  products, the package may crack, and internal stress fractures may
  occur, which shorten the lifetime of the electrical elements and can
  cause catastrophic failure. Tightening with an air driver makes a
  substantial impact. In addition, a screw torque higher than the set
  torque can be applied and the package may be damaged. Therefore,
  an electric driver is recommended.

When the package is tightened at two or more places, first pre-tighten with a lower torque at all places, then tighten with the specified torque. When using a power driver, torque control is mandatory.

#### Soldering

- When soldering the products, please be sure to minimize the working time, within the following limits:
  - 260±5°C 10±1 s (Flow, 2 times) 380±10°C 3.5±0.5 s (Soldering iron, 1 time)
- Soldering should be at a distance of at least 2.0 mm from the body of the products.

#### **Electrostatic Discharge**

- When handling the products, the operator must be grounded. Grounded wrist straps worn should have at least 1 M $\Omega$  of resistance from the operator to ground to prevent shock hazard, and it should be placed near the operator.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons or the solder bath must be grounded in order to prevent leak voltages generated by them from being applied to the products.
- The products should always be stored and transported in Sanken shipping containers or conductive containers, or be wrapped in aluminum foil

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